

HIGH-SPEED 36K (4K x 9-BIT) SYNCHRONOUS PIPELINED DUAL-PORT SRAM

Features

- Architecture based on Dual-Port SRAM cells

 Allows full simultaneous access from both ports
- High-speed clock-to-data output times
 Commercial: 8/10/12ns (max.)
- Low-power operation
 - IDT709149S Active: 1500mW (typ.)
- Standby: 75mW (typ.)

 4K X 9 bits
- Synchronous operation
 - 4ns setup to clock, 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers

Functional Block Diagram

- Fast 8ns clock to data out

- 13ns cycle time, 76MHz operation in pipeline mode
 Self-timed write allows for fast cycle times
- TTL-compatible, singles 5V (±10%) power supply
- Clock Enable feature
- Guaranteed data output hold times
- Industrial temperature range (-40°C to +85°C) is available for selected speeds.

Description

The IDT709149 is a high-speed 4K x 9 bit synchronous Dual-Port SRAM. The memory array is based on Dual-Port memory cells to allow simultaneous access from both ports. Registers on control, data, and address inputs provide low set-up and hold times. The timing latitude provided by this approach will allow systems to be designed with very



3494 drw 01

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High-Speed 36K (4K x 9-bit) Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

short cycle times. This device has been optimized for applications having unidirectional data flow or bi-directional data flow in bursts, by utilizing input data registers.

The IDT709149 utilizes a 9-bit wide data path to allow for parity at the user's option. This feature is especially useful in data communication applications where it is necessary to use a parity bit for transmission/reception error checking. Fabricated using IDT's CMOS high-performance technology, these Dual-Ports typically operate on only 800mW of power at maximum high-speed clock-to-data output times as fast as 8ns. An automatic power down feature, controlled by \overline{CE} , permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT709149 is packaged in an 80-pin TQFP.

Reference 71 70 69 68 67 66 65 64 63 62 73 72 N/C N/C 60 A_{6L} 59 A7R A7L C 58 A8R A_{8L} 57 A_{9R} A_{9L} 56 A10R A10L A11R 55 A11L 54 N/C IDT709149PF N/C 53 **OE**R PN80-1⁽⁴⁾ OEL 52 **FT/PIPED**R Vcc 🕻 10 51 GND 80-Pin TQFP 50 ⊐ GND Top View⁽⁵⁾ R/₩L ⊏ 12 49 R/\overline{W}_R N/C N/C 48 13 N/C N/C 47 CEL CER 46 15 GND -16 45 GND 17 44 I/O_{8R} I/O7∟ ⊏ 43 18 I/O7R I/O_{6L} ⊏ 42 19 I/O_{6R} N/C □ 41 20 N/C 30 31 32 33 34 35 36 37 38 39 22 23 24 28 29 Ш 3494 drw 02

Pin Configurations^(1,2,3)

NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4, This package code is used to reference the package diagram.
- 5. This text does not indicate the orientaion of the actual part-marking.

High-Speed 36K (4K x 9-bit) Synchronous Pipelined Dual-Port Static RAM

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
VTERM ⁽²⁾	Terminal Voltage	-0.5 to Vcc	V
TBIAS	Temperature Under Bias	-55 to +125	۰C
Tstg	Storage Temperature	-55 to +125	°C
IOUT	DC Output Current	50	mA

Absolute Maximum Ratings⁽¹⁾

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Symbol	Parameter	Conditions	Max.	Unit	
Ciℕ	Input Capacitance	V _{IN} = 3dV	8	pF	
Соит	Output Capacitance	Vout = 3dV	9	pF	
3					

Capacitance (TA = +25°C, f = 1.0MHz)

NOTES:

 These parameters are determined by device characterization, but are not production tested.

 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%
	-		3494 tbl 02

NOTES:

3494 tbl 01

1. This is the parameter TA.

Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V⊪	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5(1)	_	0.8	V

3494 tbl 03

3494 tbl 05

NOTES:

1. $V_{IL} \ge -1.5V$ for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			709149S		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
LI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc	_	10	μA
LO	Output Leakage Current	Vout = 0V to Vcc	_	10	μA
Vol	Output Low Voltage	loL = +4mA	_	0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4		V

NOTE:

1. At Vcc \leq 2.0V, input leakages are undefined

High-Speed 36K (4K x 9-bit) Synchronous Pipelined Dual-Port Static RAM

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^($\dot{4}$,5) (Vcc = 5V ± 10%)

				709149S8 Com'l Only		709149S10 Com'l Only		709149S12 Com'l Only		
Symbol	Parameter	Test Condition	Version	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit
lcc	Dynamic Operating Current	\overline{CE}_{L} and $\overline{CE}_{R} = VIL$,	COM'L		320		310		300	mA
	(Both Ports Active)	Outputs Open f = fMAX ⁽¹⁾	IND							
I SB1	Standby Current	\overline{CEL} and $\overline{CER} = VH$	COM'L	_	150		150	_	140	mA
	(Both Ports - TTL Level Inputs)	$f = f_{MAX}^{(1)}$	IND							
ISB2	Standby Current (One Port - TTL	$\overline{CE}^{"}A^{"} = VIL and \overline{CE}^{"}B^{"} = VIH^{(3)}$	COM'L	_	230		220		210	mA
	Level Inputs)	Active Port Outputs Open, f=fмax ⁽¹⁾	IND	-				_		
ISB 3	Full Standby Current (Both Ports - All	<u>CE</u> ∟ and CEr ≥ Vcc - 0.2V,	COM'L		15		15		15	mA
	CMOS Level Inputs)	$ \begin{array}{l} \forall \mathbb{N} \geq \text{Vcc} - 0.2 \text{V or} \\ \forall \mathbb{N} \leq 0.2 \text{V}, \ \text{f} = 0^{(2)} \end{array} $	IND							
ISB4	Full Standby Current	$\overline{CE}^{"A"} \leq 0.2V$ and	COM'L		220		210	_	200	mA
	(One Port - All CMOS Level Inputs)									

NOTES:

3494 tbl 06

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tCLK, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Vcc = 5V, TA = 25°C for Typ, and are not production tested. Icc pc = 150mA (Typ).

5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

AC Test Conditions



Figure 3. Typical Output Derating (Lumped Capacitive Load).

*Including scope and jig.

AC Electrical Characteristics Over the Operating Temperature Range—(Read and Write Cycle Timing)⁽⁴⁾

(Commercial: Vcc = 5V ± 10%, TA = 0°C to +70°C)

			49S8 I Only		49S10 I Only		24S12 I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽³⁾	16		20		20		ns
tCYC2	Clock Cycle Time (Pipelined) ⁽³⁾	13		15		16	_	ns
tCH1	Clock High Time (Flow-Through) ⁽³⁾	6		7		8	_	ns
taL1	Clock Low Time (Flow-Through) ⁽³⁾	6		7		8	_	ns
tCH2	Clock High Time (Pipelined) ⁽³⁾	6		6		6	_	ns
tCL2	Clock Low Time (Pipelined) ⁽³⁾	6		6		6	_	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽³⁾	_	12	—	15		20	ns
tCD2	Clock to Data Valid (Pipelined) ⁽³⁾	_	8	—	10		12	ns
ts	Registered Signal Set-up Time	4		4		5		ns
tH	Registered Signal Hold Time	1		1		1	_	ns
tрс	Data Output Hold After Clock High	1		1		1	_	ns
tCKLZ	Clock High to Output Low-Z ^(1,2)	2		2		2	_	ns
tскнz	Clock High to Output High-Z ^(1,2)		7	_	7		9	ns
tOE	Output Enable to Output Valid	—	8	-	8	_	10	ns
toLz	Output Enable to Output Low-Z ^(1,2)	0		0		0		ns
tонz	Output Disable to Output High-Z ^(1,2)		7	_	7		9	ns
tscк	Clock Enable, Disable Set-Up Time	4		4		5	—	ns
tнск	Clock Enable, Disable Hold Time	1		1		1		ns
tcwdd	Write Port Clock High to Read Data Delay		25		30	_	35	ns

NOTES:

3494 tbl 08

1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

3. The Pipelined output parameters (tcvc2, tcb2) always apply to the Left Port. The Right Port uses the Pipelined tcvc2 and tcb2 when FT/PIPEDR = VIH and the Flow-Through parameters (tcvc1, tcb1) when FT/PIPEDR = VIL.

4. Industrial temperature: for specific speeds, packages and powers contact your sales office.









NOTES:

- 2. $\overline{CE}L = \overline{CE}R = VIL, \overline{CLKEN}L = \overline{CLKEN}R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port, port 'R'.

^{1.} Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

Timing Waveform of Read Cycle for Pipelined Operation (Left Port; Right Port when $\overline{FT}/Piped_R = VIH$)⁽³⁾



NOTES:

1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.

3. $\overline{\text{CLKENL}}$ and $\overline{\text{CLKENR}}$ = VIL.

Timing Waveform of Pipelined Read-to-Write-to-Read (OE = VIL)



Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)



NOTES:

- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

IDT709149S

High-Speed 36K (4K x 9-bit) Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Functional Description

The IDT709149 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide very short set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal. An asynchronous output enable is provided to ease asynchronous bus interfacing.

The internal write pulse width is dependent only on the low to high transitions of the clock signal to initiate a write allowing the shortest

possible realized cycle times. Clock enable inputs are provided to stall the operation of the address and data input registers without introducing clock skew for very fast interleaved memory applications.

A HIGH on the CE input for one clock cycle will power down the internal circuitry to reduce static power consumption.

When piplelined mode is enabled, two cycles are required with $\overline{\text{CE}}$ LOW to reactivate the outputs.

		Inputs		Outputs	
Sy	nchronou	s ⁽³⁾	Asynchronous		
CLK	ĒĒ	R/W	ŌĒ	I/O0-8	Mode
\uparrow	Н	Х	Х	High-Z	Deselected—Power Down
\uparrow	L	L	Х	DATAℕ	Selected and Write Enable
\uparrow	L	Н	L	DATAOUT	Read Selected and Data Output Enabled Read (1 Latency)
\uparrow	Х	Х	Н	High-Z	Data I/O Disabled

Truth Table I: Read/Write Control⁽¹⁾

3494 tbl 09

3494 tbl 10

Truth Table II: Clock Enable Function Table⁽¹⁾

	Inp	Inputs		r Inputs	Register Outputs ⁽⁴⁾		
Operating Mode	CLK ⁽³⁾	CLKEN ⁽²⁾	ADDR	DATAIN	ADDR	DATAOUT	
Load "1"	\uparrow	L	Н	Н	Н	Н	
Load "0"	\uparrow	L	L	L	L	L	
Hold (do nothing)	\uparrow	Н	Х	Х	NC	NC	
	Х	Н	Х	Х	NC	NC	

NOTES:

1. 'H' = HIGH voltage level steady state, 'h' = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'L' = LOW voltage level steady state 'l' = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'X' = Don't care, 'NC' = No change

2. CLKEN = VIL must be clocked in during Power-Up.

3. Control signals are initialted and terminated on the rising edge of the CLK, depending on their input level. When R/W and CE are LOW, a write cycle is initiated on the LOW-to-HIGH transition of the CLK. Termination of a write cycle is done on the next LOW-to-HIGH transistion of the CLK.

4. The register outputs are internal signals from the register inputs being clocked in or disabled by CLKEN.

Ordering Information



NOTE:

1. Industrial temperature range is available.

For specific speeds, packages and poewrs contact your sales office.

Datasheet Document History

3/8/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Added additional notes to pin configurations
6/3/99:	Changed drawing format
9/1/99:	Removed Preliminary



CORPORATE HEADQUARTERS 2975 Stender Way Santa Clara, CA 95054

for SALES:

800-345-7015 or 408-727-6116 fax: 408-492-8674 www.idt.com for Tech Support: 831-754-4613 DualPortHelp@idt.com

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